

ABSTRACT OF THE DISCLOSURE

In a region where a light-receiving face of a photodiode is located, when a first interconnection and a second interconnection are patterned, respective layers are removed. After a second interlayer insulating film
5 and a cover insulating film are formed respectively as well, respective layers are removed. On the other hand, a protection insulating film is not removed by etching in the region where the light-receiving face of the photodiode is located, and an antireflection coating is still covered with the protection insulating film. Thus, a semiconductor device attaining
10 reduction in the number of process steps without lowering light reflectivity, as well as an optical device can be obtained.